

General Description

SFGMOS[®] MOSFET is based on Oriental Semiconductor's unique device design to achieve low $R_{DS(ON)}$, low gate charge, fast switching and excellent avalanche characteristics. The high V_{th} series is specially optimized for high systems with gate driving voltage greater than 10V.

Features

- Low $R_{DS(ON)}$ & FOM
- Extremely low switching loss
- Excellent stability and uniformity
- Fast switching and soft recovery



Applications

- Switched mode power supply
- Motor driver
- Battery protection
- DC-DC convertor
- Solar inverter
- UPS and energy inverter

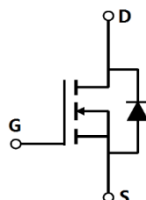
Key Performance Parameters

Parameter	Value	Unit
$V_{DS, min} @ T_{j(max)}$	150	V
$I_D, pulse$	390	A
$R_{DS(ON), max} @ V_{GS}=10V$	8	m Ω
Q_g	88	nC

Marking Information

Product Name	Package	Marking
SFG130N15PF	TO220	SFG130N15P

Package & Pin information



Absolute Maximum Ratings at $T_j=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Value	Unit
Drain source voltage	V_{DS}	150	V
Gate source voltage	V_{GS}	± 20	V
Continuous drain current ¹⁾ , $T_C=25^\circ\text{C}$	I_D	130	A
Pulsed drain current ²⁾ , $T_C=25^\circ\text{C}$	$I_{D, pulse}$	390	A
Continuous diode forward current ¹⁾ , $T_C=25^\circ\text{C}$	I_S	130	A
Diode pulsed current ²⁾ , $T_C=25^\circ\text{C}$	$I_{S, pulse}$	390	A
Power dissipation ³⁾ , $T_C=25^\circ\text{C}$	P_D	140	W
Single pulsed avalanche energy ⁵⁾	E_{AS}	110	mJ
Operation and storage temperature	T_{stg}, T_j	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal resistance, junction-case	$R_{\theta JC}$	0.89	$^\circ\text{C/W}$
Thermal resistance, junction-ambient ⁴⁾	$R_{\theta JA}$	62	$^\circ\text{C/W}$

Electrical Characteristics at $T_j=25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Drain-source breakdown voltage	BV_{DSS}	150			V	$V_{GS}=0\text{ V}, I_D=250\ \mu\text{A}$
Gate threshold voltage	$V_{GS(th)}$	2.0		4.0	V	$V_{DS}=V_{GS}, I_D=250\ \mu\text{A}$
Drain-source on-state resistance	$R_{DS(ON)}$		7.5	8.0	$\text{m}\Omega$	$V_{GS}=10\text{ V}, I_D=20\text{ A}$
Gate-source leakage current	I_{GSS}			100	nA	$V_{GS}=20\text{ V}$
				-100		$V_{GS}=-20\text{ V}$
Drain-source leakage current	I_{DSS}			1	μA	$V_{DS}=150\text{ V}, V_{GS}=0\text{ V}$
Gate resistance	R_G		4.8		Ω	$f=1\text{ MHz}, \text{Open drain}$

Dynamic Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Input capacitance	C_{iss}		8057		pF	$V_{GS}=0\text{ V}$, $V_{DS}=50\text{ V}$, $f=100\text{ kHz}$
Output capacitance	C_{oss}		737		pF	
Reverse transfer capacitance	C_{rss}		8.9		pF	
Turn-on delay time	$t_{d(on)}$		32.5		ns	$V_{GS}=10\text{ V}$, $V_{DS}=50\text{ V}$, $R_G=2.5\ \Omega$, $I_D=25\text{ A}$
Rise time	t_r		15.7		ns	
Turn-off delay time	$t_{d(off)}$		91		ns	
Fall time	t_f		20.8		ns	

Gate Charge Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Total gate charge	Q_g		88		nC	$V_{GS}=10\text{ V}$, $V_{DS}=50\text{ V}$, $I_D=25\text{ A}$
Gate-source charge	Q_{gs}		30.1		nC	
Gate-drain charge	Q_{gd}		15.2		nC	
Gate plateau voltage	$V_{plateau}$		5		V	

Body Diode Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Diode forward voltage	V_{SD}			1.3	V	$I_S=20\text{ A}$, $V_{GS}=0\text{ V}$
Reverse recovery time	t_{rr}		162		ns	$V_R=50\text{ V}$, $I_S=25\text{ A}$, $di/dt=100\text{ A}/\mu\text{s}$
Reverse recovery charge	Q_{rr}		774		nC	
Peak reverse recovery current	I_{rrm}		8.3		A	

Note

- 1) Calculated continuous current based on maximum allowable junction temperature.
- 2) Repetitive rating; pulse width limited by max. junction temperature.
- 3) P_d is based on max. junction temperature, using junction-case thermal resistance.
- 4) The value of $R_{\theta JA}$ is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with $T_a=25\text{ }^\circ\text{C}$.
- 5) $V_{DD}=50\text{ V}$, $V_{GS}=10\text{ V}$, $L=0.3\text{ mH}$, starting $T_j=25\text{ }^\circ\text{C}$.

Electrical Characteristics Diagrams

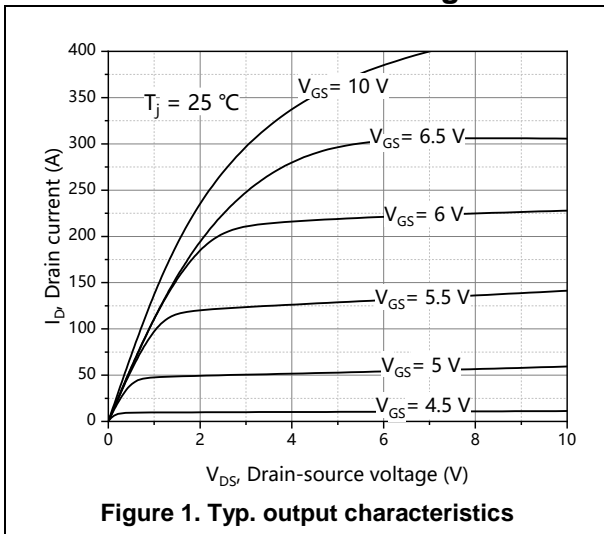


Figure 1. Typ. output characteristics

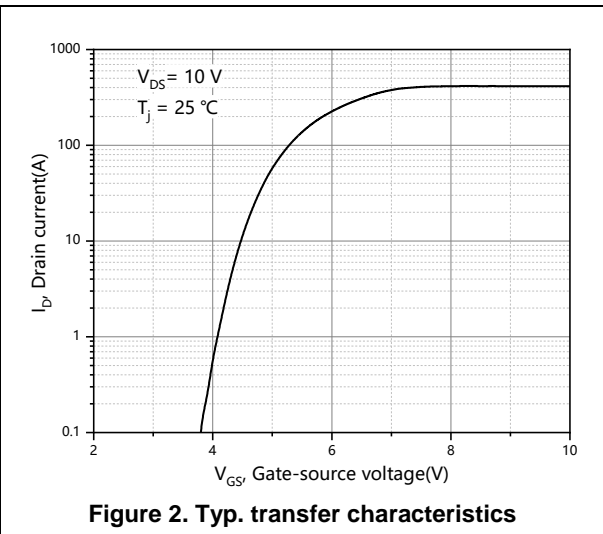


Figure 2. Typ. transfer characteristics

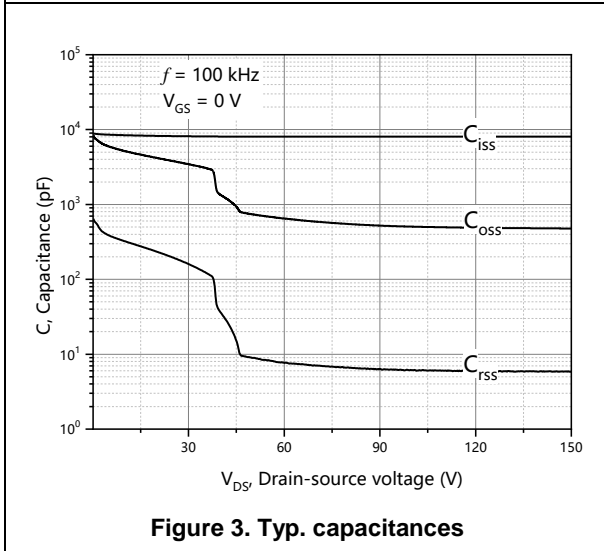


Figure 3. Typ. capacitances

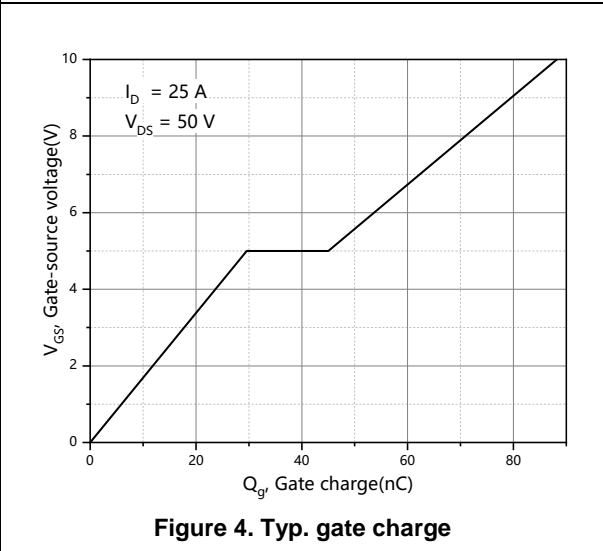


Figure 4. Typ. gate charge

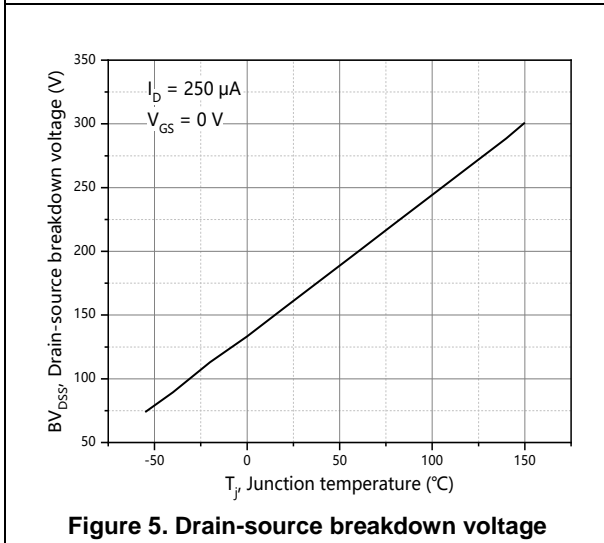


Figure 5. Drain-source breakdown voltage

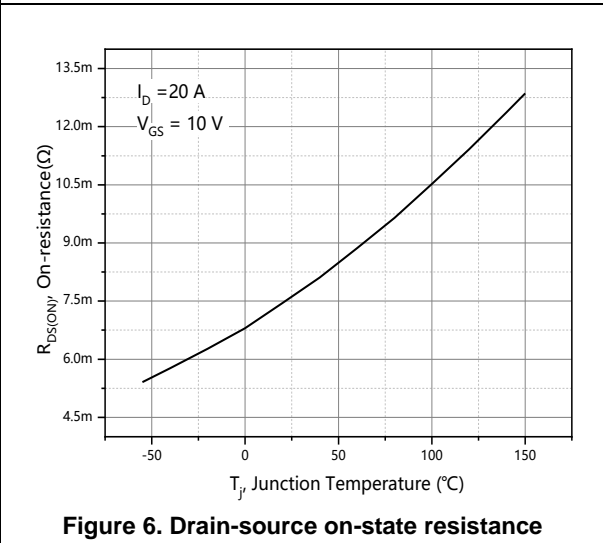
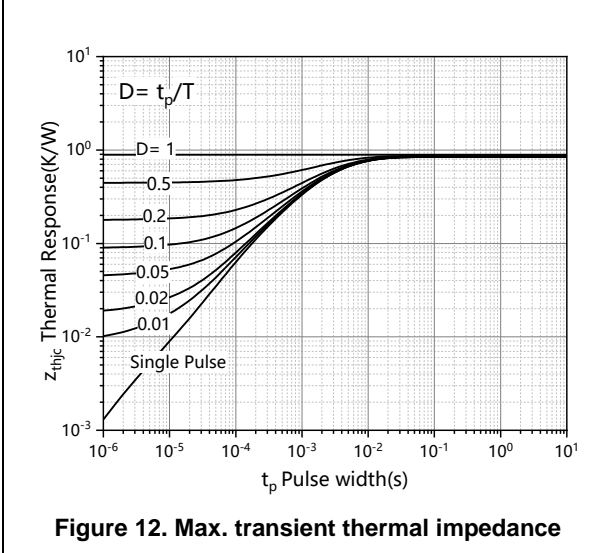
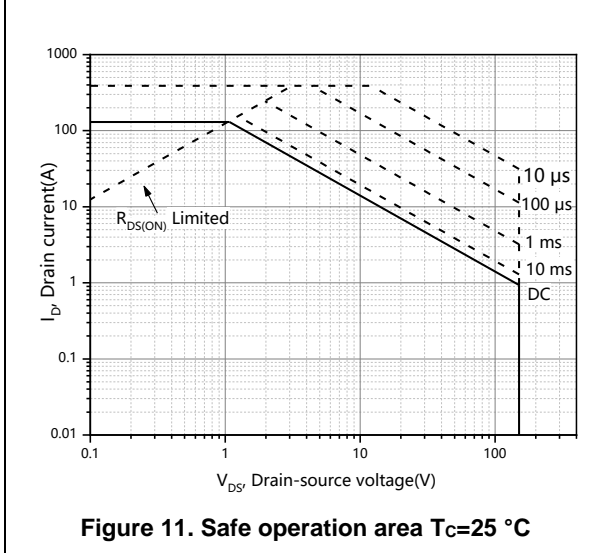
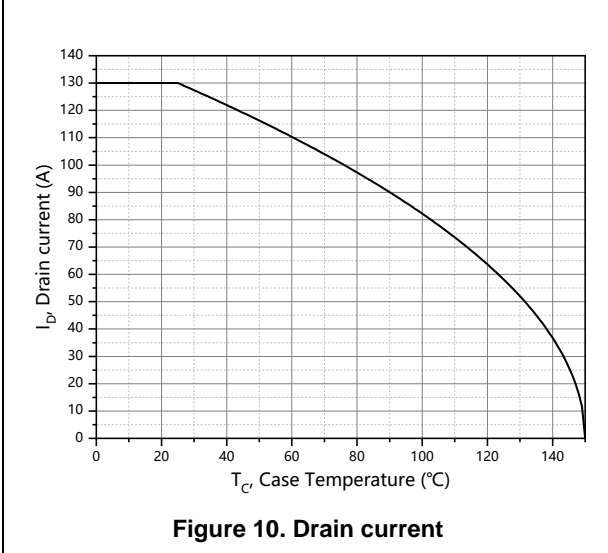
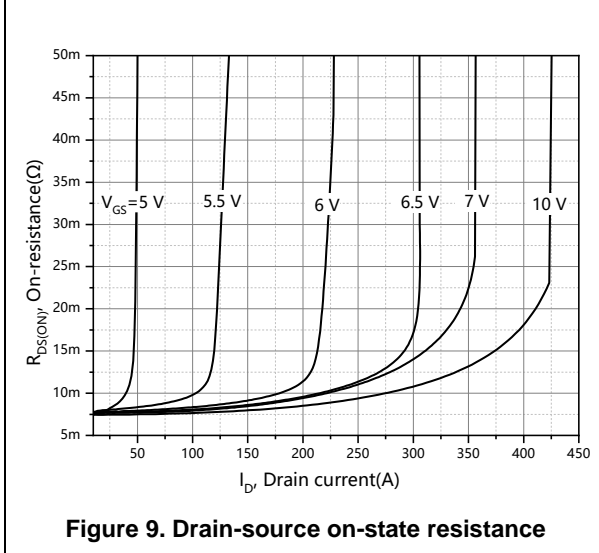
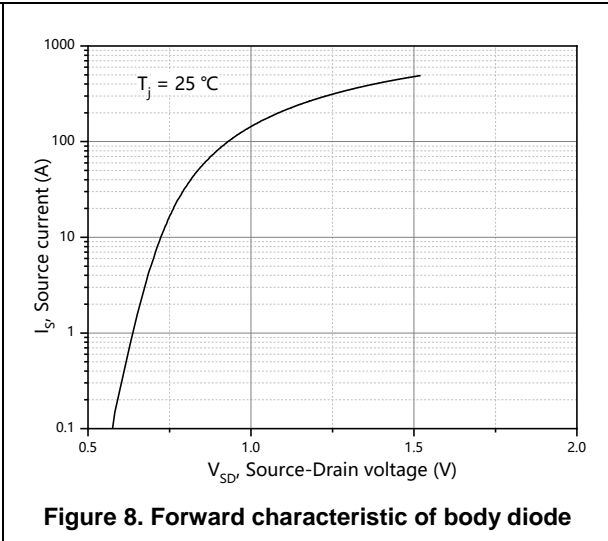
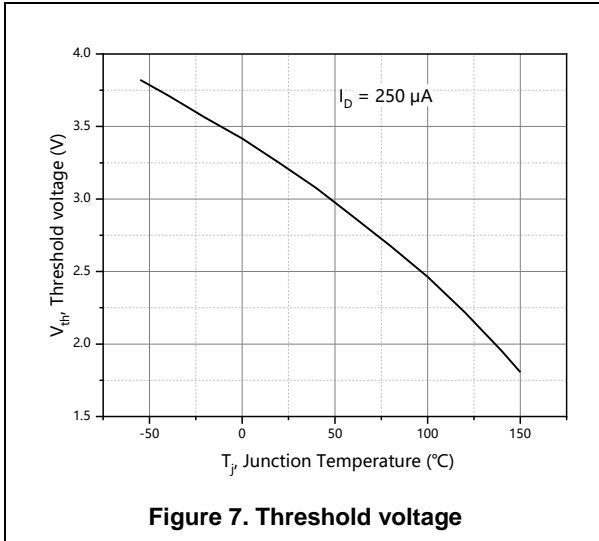


Figure 6. Drain-source on-state resistance



Test circuits and waveforms



Figure 1. Gate charge test circuit & waveform



Figure 2. Switching time test circuit & waveforms

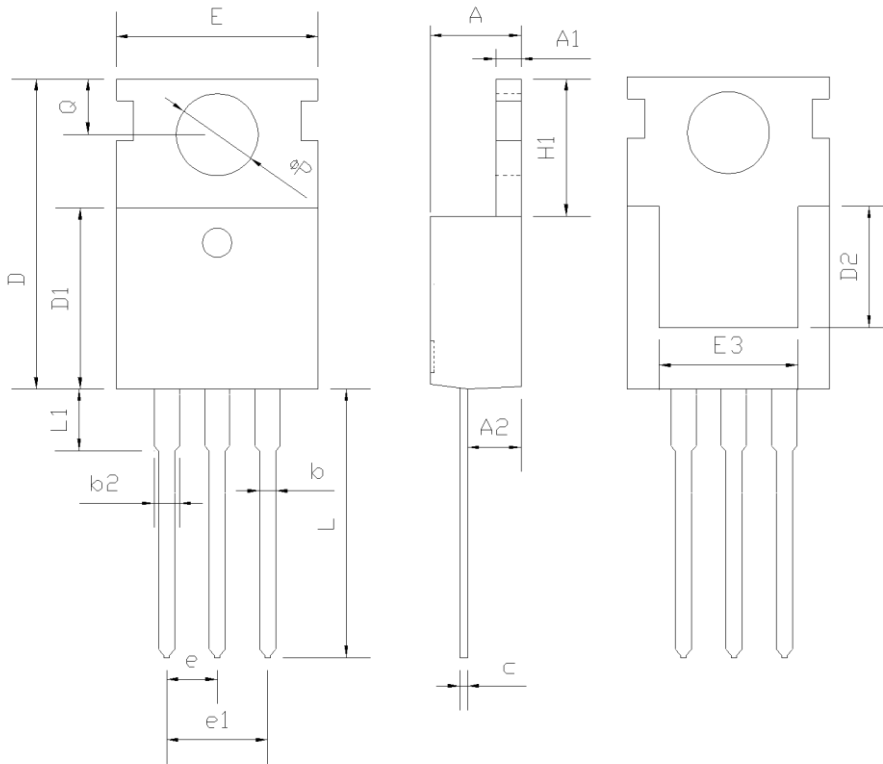


Figure 3. Unclamped inductive switching (UIS) test circuit & waveforms



Figure 4. Diode reverse recovery test circuit & waveforms

Package Information



Symbol	mm		
	Min	Nom	Max
A	4.37	4.57	4.77
A1	1.25	1.30	1.45
A2	2.20	2.40	2.60
b	0.70	0.80	0.95
b2	1.17	1.27	1.47
c	0.40	0.50	0.65
D	15.10	15.60	16.10
D1	8.80	9.10	9.40
D2	5.50	-	-
E	9.70	10.00	10.30
E3	7.00	-	-
e	2.54 BSC		
e1	5.08 BSC		
H1	6.25	6.50	6.85
L	12.75	13.50	13.80
L1	-	3.10	3.40
ΦP	3.40	3.60	3.80
Q	2.60	2.80	3.00

Version 1: TO220-C package outline dimension

Ordering Information

Package Type	Units/ Tube	Tubes / Inner Box	Units/ Inner Box	Inner Boxes/ Carton Box	Units/ Carton Box
TO220-C	50	20	1000	6	6000

Product Information

Product	Package	Pb Free	RoHS	Halogen Free
SFG130N15PF	TO220	yes	yes	yes

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